

2550 Gray Falls Dr., Suite#128, Houston, TX, 77077 USA TEL: 1-281-870-8822 EMAIL:Sales@DynamicEng.com

Features and Benefits

Frequency Range 10 MHz to 1450 MHz Output Frequency to six decimal places Output Frequency Examples: 12.688375 MHz ; 125.345678 MHz 7 mm x 5.0 mm x 1.80 mm ceramic SMD 6-pad ±50 ppm total stability over -40°C to 85°C 1 to 1.5 pico-second phase jitter (12KHz to 20 MHz) LVPECL outputs 2.5V supply

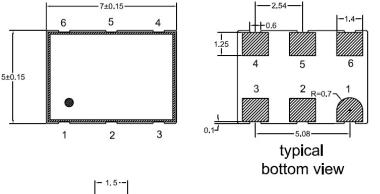
Typical Applications

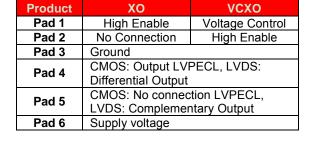
Gb Ethernet, SONET, Fibre channel, FPGA, and A/D clock reference devices

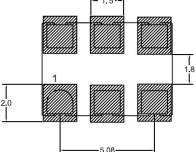
Description

A new generation of low jitter / low power clock oscillators has been developed using the latest low noise integrated circuit topologies.

Mechanical Drawing & Pin Connections







1.8MAX



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Specifications

Output Logic Type LVPECL Frequency Range 10 ~ 1450 MHz Load Differential Power Supply Voltage (V ₀₀) Volp = +2.5V D.C. ± 5% Output "High" Voltage; V ₀₄ Voltage (V ₀₀) 1.03 V Typical .0.6 V max. Output "Low" Voltage; V ₀₄ Voltage (V ₀₀) 1.85 V Typical .0.6 V max. Frequency Stability Voltage (V ₀₀) 1.85 V Typical .0.6 V max. Duty Cycle S0% ± 5% Voltage (V ₀₀) Rise Time (Tr)Fall Time (Tf) 0.25. typ 0.5n S. max. - (20% V ₀₀ - 80% V ₀₀) 100 MHz: 46 mA - Current Consumption V ₀₀ = ±2.5V 500 MHz: 58 mA - V ₀₀ = ±2.5V 500 MHz: 58 mA - All values are typical and over operating temperatures. 10 mS max. - 1 GFlz:60 mA - - - OE Pad Input XOS: Pad 1 70% of V ₀₀ maximum to disable output (high impedance). LVCMOS/LVTTL level. OVEX VS: Pad 2 70% of V ₀₀ maximum to disable output (high impedance). LVCMOS/LVTTL level. Output Enable Time Voutput Enable Time Son smax. 1.0 pS typical; 1.5 pS max. Phase Jitter, rms (12 KHz to 20	General Specifications	• at Ta=+1	25°C		
Frequency Range 10 ~ 1450 MHz Load Differential Power Supply Voltage (V ₀₀) V ₀₀ = +2.6V D.C. ± 5% Output "Low" Voltage; V _{0L} Voltage (V ₀₀) Output "Low" Voltage; V _{0L} Voltage (V ₀₀) Duty Cycle 50% + 5% Duty Cycle 50% + 5% Current Consumption 250 MHz: 48 mA V ₀₀ = +2.6V 500 MHz: 48 mA All values are typical and over operating temperatures. 100 MHz: 48 mA TH2:60 mA 250 MHz: 65 mA Current With Output Disabled 16 mA typical Start-up Time 10 ms max. Aging ±2 ppm max. first year at 25°C; ±10 ppm max. over 10 years Output Enable Time 200 ns max. Output Enable Time 20 ns max. Output Enable Time 10 ps typical; 1.5 pS max. Phase Jitter, rms (12 KHz to 20 MHz) 1.0 pS typical; 1.5 pS max. Phase Jitter, rms (12 KHz to 20 MHz) 1.0 pS typical; 1.5 pS max. Phase Jitter, rms (12 KHz to 20 MHz) 1.0 pS typical; 1.5 pS max. Phase Jitter, rms (12 KHz to 20 MHz) 1.0 pS typical; 1.5 pS max. Phase Jitter, rms (12 KHz to 20 MHz) 1.0 pS typical; 1.5 pS max.					
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Output "Low" Voltage (VoL) Voltage (VoD) 1.85 V Typical , 1.6 V min. Frequency Stability ±50 ppm over -40°C to 85°C Over all conditions	Power Supply Voltage (V _{DD})		VDD - 12.0V D.O. ± 070		
Frequency Stability ±50 ppm over -40°C to 85°C Over all conditions Duty Cycle 50% ± 5% Rise Time (Tr//Fail Time (Tf) (20% V _{DD} - 80% V _{DD}) 0.2nS. typ. 0.5nS. max. Current Consumption V _{DD} = ±.5V 100 MHz: 46 mA Current with Output Disabled 500 MHz: 65 mA 1 GHz: 60 mA 1 2 opm max. first year at 25°C; ±10 ppm max. over 10 years Output Enable Time 200 ns max. Output Enable Time 200 ns max. Output Enable Time 10 pS typical; 1.5 pS max. Phase Jitter, rms (1.8 FS MHz to 20 MHz) 1.0 pS typical; 1.5 pS max. Phase Jitter, rms (1.8 K	Output "High" Voltage; V _{он}		Voltage (V _{OD})	1.03 V Typical ,0.6 V max.	
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Resistance to Solvent MIL-STD-202, method 215 Temperature Cycling MIL-STD-883, method 1010			MIL-STD-202F method 204, 35G, 50 to	o 2000 Hz	
Temperature Cycling MIL-STD-883, method 1010	Vibration				
	Vibration Shock		MIL-STD-202F method 213B, test cond		
ESD Rating >2000 V (per MIL-STD-883, method 3015)	Vibration Shock Resistance to Solvent		MIL-STD-202F method 213B, test cond MIL-STD-202, method 215		



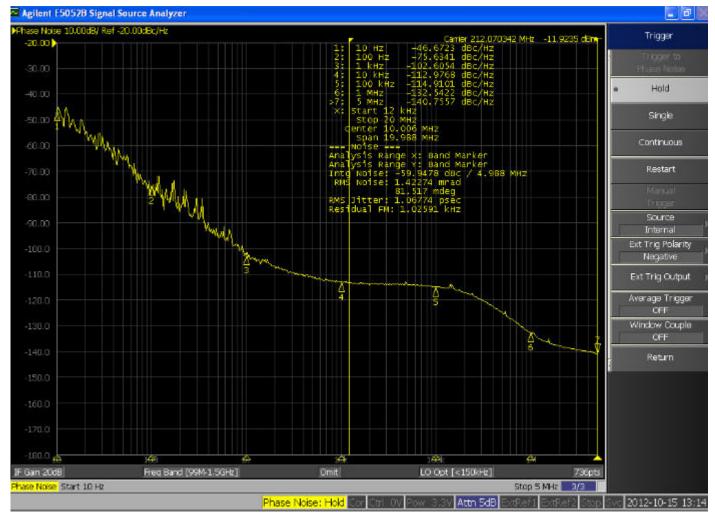
2550 Gray Falls Dr., Suite#128, Houston, TX, 77077 USA TEL: 1-281-870-8822 EMAIL:Sales@DynamicEng.com

Ordering Options:

"x MHz " examples : 125.000000 MHz ; or 12.688375 MHz ; 1250.005600 MHz

Phase Noise Graphs

212 MHz LVPECL output



Dynamic Engineers reserves the right to make changes to the company datasheet(s) along with other information contained inside; such as data tables and graphs without notification to potential customers who may have earlier revisions in their possession.



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1000 MHz LVPECL output

